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# **KSP2907A PNP General Purpose Amplifier**

### **Features**

- Collector-Emitter Voltage: VCEO= 60V
- Collector Power Dissipation: Pc (max)=625mW
- Suffix "-C" means a Center Collector (1.Emitter 2.Collector 3.Base)
- Non suffix "-C" means a Side Collector (1.Emitter 2.Base 3.Collector)
- Available as PN2907A



### Absolute Maximum Ratings \* T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V <sub>CBO</sub>	Collector-Base Voltage	-60	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	-60	V	
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V	
I <sub>C</sub>	Collector current	-600	mA	
TJ	Junction Temperature	+150	°C	
T <sub>stg</sub>	Storage Temperature	-55 ~ +150	°C	

These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.
These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

#### Thermal Characteristics T\_=25°C unless otherwise noted

Symbol	Parameter	Мах	Units	
P <sub>C</sub>	Collector Power Dissipation, by $R_{\theta JA}$	625	mW	
$R_{\theta JC}$	Thermal Resistance, Junction to Case(note1)	83.3	°C/W	
R <sub>0JA</sub>	Thermal Resistance, Junction to Ambient(note2)	200	°C/W	

Note1. Infinite heat sink.

Note2. Minimum Land pad size.

#### Electrical Characteristics \* Ta = 25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{\rm C} = -10\mu A, I_{\rm E} = 0$	-60			V
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	$I_{\rm C} = -10 {\rm mA}, I_{\rm B} = 0$	-60			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{E} = -10\mu A, I_{C} = 0$	-5.0			V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = -50V, I_{E} = 0$			-10	nA
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> = -10V, I <sub>C</sub> = -0.1mA,	75			
		$V_{CE} = -10V, I_{C} = -1mA,$	100			
		$V_{CE} = -10V, I_{C} = -10mA,$	100			
		V <sub>CE</sub> = -10V, I <sub>C</sub> = -150mA,	100		300	
		$V_{CE} = -10V, I_{C} = -500mA,$	50			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -150mA, I <sub>B</sub> = -15mA			-0.4	V
~ /		I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA			-1.6	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -150mA, I <sub>B</sub> = -15mA			-1.3	V
. ,		I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA			-2.6	V
C <sub>obo</sub>	Output Capacitance	V <sub>CB</sub> = -10V, I <sub>E</sub> = 0, f = 1.0MHz			8	pF
f <sub>T</sub>	Current Gain Bandwidth Product	$I_{\rm C} = -50 {\rm mA}, V_{\rm CE} = -20 {\rm V},$	200			MHz
		f = 100MHz				
t <sub>ON</sub>	Turn On Time	V <sub>CC</sub> = -30V, I <sub>C</sub> = -150mA, I <sub>B1</sub> = -15mA			45	ns
t <sub>OFF</sub>	Turn Off Time	$V_{CC}$ = -6V, $I_{C}$ = -150mA, $I_{B1}$ = $I_{B1}$ = -15mA			100	ns

Item are tes ted by Pulse Test: Pulse Width≤300us, Duty Cycle≤2%

## Package Marking and Ordering Information

Device(note)	Device Marking	Package	Packing Method	Qty(pcs)	Pin Definitions
KSP2907ABU	KSP2907A	TO-92	BULK		1.Emitter 2.Base 3.Collector
KSP2907ACBU	KSP2907AC	TO-92	BULK		1.Emitter 2.Collector 3.Base
KSP2907ATA	KSP2907A	TO-92	TAPE & AMMO	2,000	1.Emitter 2.Base 3.Collector
KSP2907ACTA	KSP2907AC	TO-92	TAPE & AMMO	2,000	1.Emitter 2.Collector 3.Base
KSP2907ATF	KSP2907A	TO-92	TAPE & REEL	2,000	1.Emitter 2.Base 3.Collector

Note : Affix "-C-" - center collector pin. Suffix "-BU" - Bulk packing, straight lead form.(see package dimensions) Suffix "-TF" - Tape& Reel packing, 0.200 In-Line Spacing lead form. (see package dimensions) SUffix "-TA" - Tape& AMMO packing, 0.200 In-Line Spacing lead form. (see package dimensions)

#### **Typical Characteristics** V<sub>BE</sub>(sat), V<sub>CE</sub>(sat)[V], SATURATION VOLTAGE -1 100 $V_{CE} = -10V$ $I_{\rm C} = 10 I_{\rm B}$ hFE, DC CURRENT GAIN V<sub>BE</sub>(sat) -1 100 -0.1 V<sub>CE</sub>(sat) 10 └ -1 -0.01 -10 -100 -1000 -1 -10 -100 -1000 Ic[mA], COLLECTOR CURRENT Ic[A], COLLECTOR CURRENT Figure 2. Collector-Emitter Saturation Voltage Figure 1. DC current Gain **Base-Emitter Saturation Voltage** 100 $I_{\rm E}=0$ f<sub>f</sub>[MHz], CURRENT GAIN BANDWIDTH PRODUCT f = 1MHz V<sub>CE</sub> = -20V Cob [pF], CAPACITANCE 10 10 10 └ -1 0.1 L -1 -10 -100 -1000 -10 -100 Ic[mA], COLLECTOR CURRENT V<sub>CB</sub> [V], COLLECTOR-BASE VOLTAGE Figure 3. Output Capacitance Figure 4. Current Gain Bandwidth Product



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#### **Definition of Terms**

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